



Schottky Diodes



Features

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength

- **Terminals:** Tin plated leads, solderable per JESD22-B12 and JESD22-B12

S-compli

2 ESD

IFSM

A

200

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■Electrical Characteristics $T_a=25$ Unless otherwise specified

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBR10300F
Maximum instantaneous forward voltage drop per diode	V _{FM}	V	I _{FM} =10.0A	0.975
Maximum DC reverse current at rated DC blocking voltage per diode	I _{RRM1}	mA	V _{RM} =V _R M T _a =25	0.05
	I _{RRM2}		V _{RM} =V _R M T _a =100	10

Note1:Pulse test:300uS pulse width,1% duty cycle

Note2:Pulse test:pulse width 40mS

